

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV32F** is Designed for in linear v.h.f. amplifiers of television transmitters and transporters.

FEATURES:

- Diffused emitter ballasting resistors
- $P_G = 16$ dB at 10 W/224 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	60 V
V_{CEO}	32 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	2.1 $^\circ C/W$

PACKAGE STYLE .500 6L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06
B	.045/1.14	
C	.210/5.33	.220/5.59
D	.835/21.21	.865/21.97
E	.200/5.08	.210/5.33
F	.490/12.45	.510/12.95
G	.003/0.08	.007/0.18
H	.125/3.18	
I	.720/18.29	.730/18.54
J	.970/24.64	.980/24.89
K	.095/2.41	.105/2.67
L	.150/3.81	.170/4.32
M	.280/7.11	

1= Collector 2= Base 3 and 4= Emitter

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 100$ mA	32			V
BV_{CES}	$I_C = 15$ mA	60			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 32$ V			5.0	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 1.6$ A	20		120	---
C_C	$V_{CB} = 25$ V $f = 1.0$ MHz		50		pF
P_G	$V_{CE} = 25$ V $P_{OUT} = 10$ W $f = 224$ MHz	16			dB